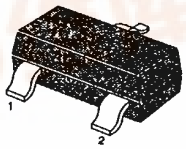
MMBA811C6 PNP EPITAXIAL SILICON TRANSISTOR

T-29-19

DRIVER TRANSISTOR

SOT-23



1. Base 2. Emitter 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	Tstg	150	°C

• Refer to MMBT5086 for graphs

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA, I_E=0	50		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1.0mA, I_B=0	45		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=10μA, I_C=0	5		V
Collector Cutoff Current	I_{CBO}	V_{CB}=40V, I_E=0		50	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5.0V, I_C=0		50	nA
DC Current Gain	h_{FE}	V_{CE}=3V, I_C=0.1mA	150		
		V_{CE}=3V, I_C=0.5mA	200	400	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=20mA, I_B=2.0mA		0.3	V
Current Gain-Bandwidth Product	f_T	I_C=1.0mA, V_{CE}=6.0V f=100MHz	75		MHz

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Marking